

**AMENDMENTS TO THE CLAIMS:**

**Listing of claims:**

This listing of claims replaces all prior versions and listings of claims in the application.

1-14. (Cancelled)

15. (Original) A method of manufacturing a semiconductor device including a capacitor including a pair of electrodes and a ferroelectric film with ferroelectricity sandwiched therebetween, the method comprising the steps of:

- (a) depositing the ferroelectric film on a first substrate;
- (b) forming the capacitor by grinding the ferroelectric film and forming the electrodes so that the electrodes are perpendicular to a direction of a polarization axis of the ferroelectric film;
- (c) forming a first interlayer insulating film covering a surface of the first substrate and the capacitor;
- (d) forming a transistor on a second substrate, the transistor including a gate electrode and a diffusion region;
- (e) forming a second interlayer insulating film covering a surface of the second substrate and the transistor;
- (f) flattening surfaces of the first and second interlayer insulating films by chemical mechanical polishing;

(g) integrating the first and second substrates by joining the flattened surfaces of the first and second interlayer insulating films; and

(h) removing the first substrate.

16. (Original) The method as claimed in claim 15, wherein the first substrate employs one of a (100) surface and a (010) surface thereof as a main surface.

17. (Original) The method as claimed in claim 16, wherein the first substrate has an inclination with an offset angle from the one of the (100) surface and the (010) surface thereof.

18. (Original) The method as claimed in claim 16, wherein the first substrate comprises MgO, SrTiO<sub>3</sub>,  $\alpha$ -Al<sub>2</sub>O<sub>3</sub>, or MgAl<sub>2</sub>O<sub>4</sub>.

19. (Original) The method as claimed in claim 15, wherein:

a buffer layer is formed on the first substrate;

the first substrate comprises a Si substrate; and

the buffer layer comprises a MgO layer, an yttrium-stabilized ZrO<sub>2</sub> layer, a SrTiO<sub>3</sub> layer, a MgAl<sub>2</sub>O<sub>4</sub> layer, or a CaO layer.

20. (Original) The method as claimed in claim 19, wherein:

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an additional buffer layer is formed on the buffer layer;

the buffer layer comprises the MgO layer; and

the additional buffer layer comprises a  $\text{SrRuO}_3$  layer, a  $\text{YBa}_2\text{Cu}_3\text{O}_{7-\delta}$  layer, or a  $\text{La}_{2-x}\text{Sr}_x\text{CuO}_4$  layer.

21. (Original) The method as claimed in claim 15, wherein:

a buffer layer is formed on the first substrate;

the first substrate comprises a Si substrate; and

the buffer layer comprises a  $\text{SrRuO}_3$  layer, a  $\text{YBa}_2\text{Cu}_3\text{O}_{7-\delta}$  layer, or a  $\text{La}_{2-x}\text{Sr}_x\text{CuO}_4$  layer.